

**IN THE CLAIMS**

Please amend the claims as follow:

1. (Currently amended) A pattern formation method comprising the steps of:  
forming, on a substrate, a resist film made from a chemically amplified resist material;  
performing pattern exposure by selectively irradiating said resist film with exposing light  
while providing, between supplying, onto said resist film [[,]] and a projection lens, a solution  
that includes an acid generator for generating an acid through irradiation with light; and  
forming a resist pattern by developing said resist film after the pattern exposure.
2. (Currently amended) The pattern formation method of Claim 1,  
wherein said solution is water or perfluoropolyether.
3. (Canceled)
4. (Original) The pattern formation method of Claim 1,  
wherein said acid generator is an onium salt.
5. (Currently amended) A pattern formation method comprising the steps of:  
forming, on a substrate, a resist film made from a chemically amplified resist material;  
performing pattern exposure by selectively irradiating said resist film with exposing light  
while providing, between supplying, onto said resist film[[,]] and a projection lens, a solution  
including an acid; and  
forming a resist pattern by developing said resist film after the pattern exposure.
6. (Currently amended) The pattern formation method of Claim 5,  
wherein said solution is water or perfluoropolyether.
7. (Canceled)
8. (Original) The pattern formation method of Claim 5,

wherein said acid is acetic acid.

9. (Currently amended) A pattern formation method comprising the steps of:  
forming, on a substrate, a resist film made from a chemically amplified resist material;  
forming, on said resist film, a water-soluble film including an acid generator for  
generating an acid through irradiation with light;  
performing pattern exposure by selectively irradiating said resist film with exposing light  
while providing supplying a nonaqueous solution [[onto]] between said water-soluble film and a  
projection lens; and

forming a resist pattern by developing said resist film after the pattern exposure.

10. (Original) The pattern formation method of Claim 9,

wherein said nonaqueous solution is perfluoropolyether.

11. (Original) The pattern formation method of Claim 9,

wherein said acid generator is an onium salt.

12. (Original) The pattern formation method of Claim 9,

wherein said water-soluble film is a polyvinyl alcohol film or polyvinyl pyrrolidone film.

13. (Currently amended) A pattern formation method comprising the steps of:

forming, on a substrate, a resist film made from a chemically amplified resist material;

forming, on said resist film, a water-soluble film including an acid;

performing pattern exposure by selectively irradiating said resist film with exposing light

while providing supplying a nonaqueous solution [[onto]] between said water-soluble film and a  
projection lens; and

forming a resist pattern by developing said resist film after the pattern exposure.

14. (Original) The pattern formation method of Claim 13,

wherein said nonaqueous solution is perfluoropolyether.

15. (Original) The pattern formation method of Claim 13,

wherein said acid is acetic acid.

16. (Original) The pattern formation method of Claim 13,

wherein said water-soluble film is a polyvinyl alcohol film or a polyvinyl pyrrolidone

film.

17. (Currently amended) A pattern formation method comprising the steps of:

forming, on a substrate, a resist film made from a chemically amplified resist material;

forming, on said resist film, a water-soluble film including an acid polymer;

performing pattern exposure by selectively irradiating said resist film with exposing light

while providing supplying a nonaqueous solution [[onto]] between said water-soluble film and a projection lens; and

forming a resist pattern by developing said resist film after the pattern exposure.

18. (Original) The pattern formation method of Claim 17,

wherein said nonaqueous solution is perfluoropolyether.

19. (Original) The pattern formation method of Claim 17,

wherein said acid polymer is polyacrylic acid or polystyrene sulfonic acid.

20. (New) The pattern formation method of Claim 1,

wherein said solution is provided directly on said resist film during said pattern exposure.

21. (New) The pattern formation method of Claim 5,

wherein said solution is provided directly on said resist film during said pattern exposure.

22. (New) The pattern formation method of Claim 9,

wherein said nonaqueous solution is provided directly on said water-soluable film during said pattern exposure.

23. (New) The pattern formation method of Claim 13,

wherein said nonaqueous solution is provided directly on said water-soluable film during said pattern exposure.

24. (New) The pattern formation method of Claim 17,

wherein said nonaqueous solution is provided directly on said water-soluable film during said pattern exposure.